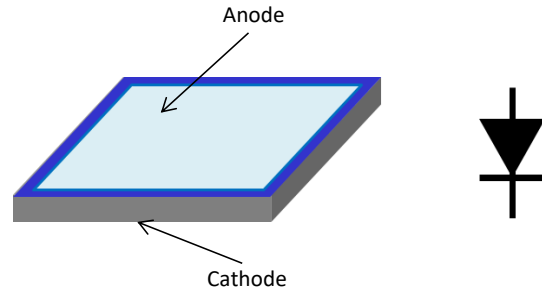


# YJ Planar Schottky Barrier Diode Die Specification

40V 0.04A, 9mil, Schottky barrier diode die based on silicon planar process  
 Part No.: PSB009L040AG-155A

## Main Products Characteristics

- Average forward current:  $I_{F(AV)} = 0.04A$
- Maximum operating junction temperature:  $T_j = 125\text{ }^\circ\text{C}$
- ESD rating: >2KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: AL/3.915um



## Maximum Ratings

Parameter	Symbol	Rating
Repetitive peak reverse voltage	$V_{RRM}$	40 V
Average forward current	$I_{F(AV)}$	0.04A
Non-repetitive peak surge current ( $t_p = 8.3\text{ ms}$ , halfwave, 1 cycle)	$I_{FSM}$	1 A
Storage temperature range	$T_{stg}$	-50 to +125 °C
Maximum operating junction temperature	$T_j$	125 °C

## Static Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	
		Spec	Typical
Reverse breakdown voltage $I_R = 100\mu\text{A}$	$V_{BR}$	45 V	52V
Maximum forward voltage drop $I_F = 0.04A$ Pulse Test: $t_p = 800\ \mu\text{s}$ , $\delta \leq 2\%$	$V_F$	1V	0.63V
Maximum reverse current $V_R = 40V$ Pulse Test: $t_p = 200\ \mu\text{s}$ , $\delta \leq 2\%$	$I_R$	0.5uA	0.07uA

## Device Schematics and Outline Drawing

Die Thickness *	155um
Die Size **	230um
Top Metal Pad	170um
Active Area	100um
Top Metal	AL/3.915um
Back Metal	Au/1.2um
Steet width	60um

## Important Notice

<p>Specification apply to die only. Actual performance may degrade when assembled.</p> <p><b>Yangjie Electronics</b> does not guarantee device performance after assembly. All operating parameters must be validated for each customer application by customer's technical experts.</p> <p>Data sheet information is subjected to change without notice.</p>	<p>Recommended Storage Environment:</p> <p>Store in original container, in dessicated nitrogen, with no contamination.</p> <p>Shelf life for parts stored in above condition is 2 years.</p> <p>If the storage is done in normal atmosphere shelf life is reduced to 6 months.</p>
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